



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



## Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



---

# ***ProASIC3 nano FPGA Fabric***

***User's Guide***



---

# Table of Contents

---

Introduction .....	7
Contents .....	7
Revision History .....	7
Related Information .....	7
<b>1 FPGA Array Architecture in Low Power Flash Devices .....</b>	<b>9</b>
Device Architecture .....	9
FPGA Array Architecture Support .....	10
Device Overview .....	11
Related Documents .....	20
List of Changes .....	20
<b>2 Low Power Modes in ProASIC3/E and ProASIC3 nano FPGAs .....</b>	<b>21</b>
Introduction .....	21
Power Consumption Overview .....	21
Static (Idle) Mode .....	22
User Low Static (Idle) Mode .....	23
Sleep Mode .....	25
Shutdown Mode .....	27
Conclusion .....	28
Related Documents .....	28
List of Changes .....	29
<b>3 Global Resources in Low Power Flash Devices .....</b>	<b>31</b>
Introduction .....	31
Global Architecture .....	31
Global Resource Support in Flash-Based Devices .....	32
VersaNet Global Network Distribution .....	33
Chip and Quadrant Global I/Os .....	35
Spine Architecture .....	41
Using Clock Aggregation .....	44
Design Recommendations .....	46
Conclusion .....	58
Related Documents .....	58
List of Changes .....	59
<b>4 Clock Conditioning Circuits in Low Power Flash Devices and Mixed Signal FPGAs .....</b>	<b>61</b>
Introduction .....	61
Overview of Clock Conditioning Circuitry .....	61
CCC Support in Microsemi's Flash Devices .....	63
Global Buffers with No Programmable Delays .....	64
Global Buffer with Programmable Delay .....	64
Global Buffers with PLL Function .....	67
Global Input Selections .....	71
Device-Specific Layout .....	78

PLL Core Specifications	84
Functional Description	85
Software Configuration	96
Detailed Usage Information	104
Recommended Board-Level Considerations	112
Conclusion	113
Related Documents	113
List of Changes	113
<b>5 FlashROM in Microsemi's Low Power Flash Devices</b>	<b>117</b>
Introduction	117
Architecture of User Nonvolatile FlashROM	117
FlashROM Support in Flash-Based Devices	118
FlashROM Applications	120
FlashROM Security	121
Programming and Accessing FlashROM	122
FlashROM Design Flow	124
Custom Serialization Using FlashROM	129
Conclusion	130
Related Documents	130
List of Changes	130
<b>6 SRAM and FIFO Memories in Microsemi's Low Power Flash Devices</b>	<b>131</b>
Introduction	131
Device Architecture	131
SRAM/FIFO Support in Flash-Based Devices	134
SRAM and FIFO Architecture	135
Memory Blocks and Macros	135
Initializing the RAM/FIFO	148
Software Support	154
Conclusion	157
List of Changes	157
<b>7 I/O Structures in nano Devices</b>	<b>159</b>
Introduction	159
Low Power Flash Device I/O Support	161
nano Standard I/Os	162
I/O Architecture	164
I/O Standards	166
Wide Range I/O Support	166
I/O Features	167
Simultaneously Switching Outputs (SSOs) and Printed Circuit Board Layout	176
I/O Software Support	177
User I/O Naming Convention	178
I/O Bank Architecture and CCC Naming Conventions	179
Board-Level Considerations	181
Conclusion	182
Related Documents	183
List of Changes	183



<b>8 I/O Software Control in Low Power Flash Devices</b> .....	<b>185</b>
Flash FPGAs I/O Support .....	186
Software-Controlled I/O Attributes .....	187
Implementing I/Os in Microsemi Software .....	188
Assigning Technologies and VREF to I/O Banks .....	198
Conclusion .....	203
Related Documents .....	203
List of Changes .....	204
<b>9 DDR for Microsemi's Low Power Flash Devices</b> .....	<b>205</b>
Introduction .....	205
Double Data Rate (DDR) Architecture .....	205
DDR Support in Flash-Based Devices .....	206
I/O Cell Architecture .....	207
Input Support for DDR .....	209
Output Support for DDR .....	209
Instantiating DDR Registers .....	210
Design Example .....	216
Conclusion .....	218
List of Changes .....	219
<b>10 Programming Flash Devices</b> .....	<b>221</b>
Introduction .....	221
Summary of Programming Support .....	221
Programming Support in Flash Devices .....	222
General Flash Programming Information .....	223
Important Programming Guidelines .....	229
Related Documents .....	231
List of Changes .....	232
<b>11 Security in Low Power Flash Devices</b> .....	<b>235</b>
Security in Programmable Logic .....	235
Security Support in Flash-Based Devices .....	236
Security Architecture .....	237
Security Features .....	238
Security in Action .....	242
FlashROM Security Use Models .....	245
Generating Programming Files .....	247
Conclusion .....	258
Glossary .....	258
References .....	258
Related Documents .....	259
List of Changes .....	259
<b>12 In-System Programming (ISP) of Microsemi's Low Power Flash Devices Using FlashPro4/3/3X</b> ...	<b>261</b>
Introduction .....	261
ISP Architecture .....	261
ISP Support in Flash-Based Devices .....	262
Programming Voltage (VPUMP) and VJTAG .....	263
Nonvolatile Memory (NVM) Programming Voltage .....	263

IEEE 1532 (JTAG) Interface .....	264
Security .....	264
Security in ARM-Enabled Low Power Flash Devices .....	265
FlashROM and Programming Files .....	267
Programming Solution .....	268
ISP Programming Header Information .....	269
Board-Level Considerations .....	271
Conclusion .....	272
Related Documents .....	272
List of Changes .....	273
<b>13 Core Voltage Switching Circuit for IGLOO and ProASIC3L In-System Programming .....</b>	<b>275</b>
Introduction .....	275
Microsemi's Flash Families Support Voltage Switching Circuit .....	276
Circuit Description .....	277
Circuit Verification .....	278
DirectC .....	280
Conclusion .....	280
List of Changes .....	281
<b>14 Microprocessor Programming of Microsemi's Low Power Flash Devices .....</b>	<b>283</b>
Introduction .....	283
Microprocessor Programming Support in Flash Devices .....	284
Programming Algorithm .....	285
Implementation Overview .....	285
Hardware Requirement .....	288
Security .....	288
Conclusion .....	289
List of Changes .....	290
<b>15 Boundary Scan in Low Power Flash Devices .....</b>	<b>291</b>
Boundary Scan .....	291
TAP Controller State Machine .....	291
Microsemi's Flash Devices Support the JTAG Feature .....	292
Boundary Scan Support in Low Power Devices .....	293
Boundary Scan Opcodes .....	293
Boundary Scan Chain .....	293
Board-Level Recommendations .....	294
Advanced Boundary Scan Register Settings .....	295
List of Changes .....	296
<b>16 UJTAG Applications in Microsemi's Low Power Flash Devices .....</b>	<b>297</b>
Introduction .....	297
UJTAG Support in Flash-Based Devices .....	298
UJTAG Macro .....	299
UJTAG Operation .....	300
Typical UJTAG Applications .....	302
Conclusion .....	306
Related Documents .....	306
List of Changes .....	306

<b>17 Power-Up/-Down Behavior of Low Power Flash Devices</b> .....	<b>307</b>
Introduction .....	307
Flash Devices Support Power-Up Behavior .....	308
Power-Up/-Down Sequence and Transient Current .....	309
I/O Behavior at Power-Up/-Down .....	311
Cold-Sparing .....	316
Hot-Swapping .....	317
Conclusion .....	317
Related Documents .....	318
List of Changes .....	318
<b>A Summary of Changes</b> .....	<b>319</b>
History of Revision to Chapters .....	319
<b>B Product Support</b> .....	<b>321</b>
Customer Service .....	321
Customer Technical Support Center .....	321
Technical Support .....	321
Website .....	321
Contacting the Customer Technical Support Center .....	321
ITAR Technical Support .....	322
<b>Index</b> .....	<b>323</b>

# Introduction

---

## Contents

This user's guide contains information to help designers understand and use Microsemi's ProASIC<sup>®</sup>3 nano devices. Each chapter addresses a specific topic. Most of these chapters apply to other Microsemi device families as well. When a feature or description applies only to a specific device family, this is made clear in the text.

## Revision History

The revision history for each chapter is listed at the end of the chapter. Most of these chapters were formerly included in device handbooks. Some were originally application notes or information included in device datasheets.

A "Summary of Changes" table at the end of this user's guide lists the chapters that were changed in each revision of the document, with links to the "List of Changes" sections for those chapters.

## Related Information

Refer to the *ProASIC3 nano Low Power Flash FPGAs* datasheet for detailed specifications, timing, and package and pin information.

The website for ProASIC3 nano devices is [/www.microsemi.com/soc/products/pa3nano/default.aspx](http://www.microsemi.com/soc/products/pa3nano/default.aspx).





---

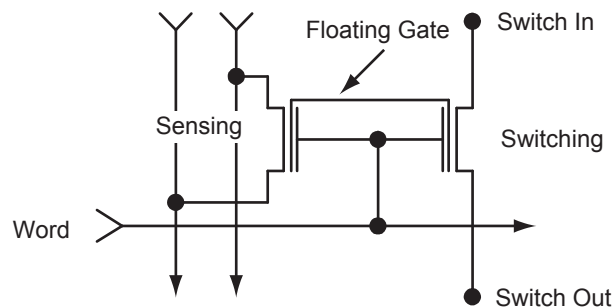
# 1 – FPGA Array Architecture in Low Power Flash Devices

---

## Device Architecture

### Advanced Flash Switch

Unlike SRAM FPGAs, the low power flash devices use a live-at-power-up ISP flash switch as their programming element. Flash cells are distributed throughout the device to provide nonvolatile, reconfigurable programming to connect signal lines to the appropriate VersaTile inputs and outputs. In the flash switch, two transistors share the floating gate, which stores the programming information (Figure 1-1). One is the sensing transistor, which is only used for writing and verification of the floating gate voltage. The other is the switching transistor. The latter is used to connect or separate routing nets, or to configure VersaTile logic. It is also used to erase the floating gate. Dedicated high-performance lines are connected as required using the flash switch for fast, low-skew, global signal distribution throughout the device core. Maximum core utilization is possible for virtually any design. The use of the flash switch technology also removes the possibility of firm errors, which are increasingly common in SRAM-based FPGAs.



---

**Figure 1-1 • Flash-Based Switch**

## FPGA Array Architecture Support

The flash FPGAs listed in [Table 1-1](#) support the architecture features described in this document.

**Table 1-1 • Flash-Based FPGAs**

Series	Family*	Description
IGLOO®	IGLOO	Ultra-low power 1.2 V to 1.5 V FPGAs with Flash*Freeze technology
	IGLOOe	Higher density IGLOO FPGAs with six PLLs and additional I/O standards
	IGLOO nano	The industry's lowest-power, smallest-size solution
	IGLOO PLUS	IGLOO FPGAs with enhanced I/O capabilities
ProASIC®3	ProASIC3	Low power, high-performance 1.5 V FPGAs
	ProASIC3E	Higher density ProASIC3 FPGAs with six PLLs and additional I/O standards
	ProASIC3 nano	Lowest-cost solution with enhanced I/O capabilities
	ProASIC3L	ProASIC3 FPGAs supporting 1.2 V to 1.5 V with Flash*Freeze technology
	RT ProASIC3	Radiation-tolerant RT3PE600L and RT3PE3000L
	Military ProASIC3/EL	Military temperature A3PE600L, A3P1000, and A3PE3000L
	Automotive ProASIC3	ProASIC3 FPGAs qualified for automotive applications
Fusion	Fusion	Mixed signal FPGA integrating ProASIC3 FPGA fabric, programmable analog block, support for ARM® Cortex™-M1 soft processors, and flash memory into a monolithic device

*Note:* \*The device names link to the appropriate datasheet, including product brief, DC and switching characteristics, and packaging information.

### **IGLOO Terminology**

In documentation, the terms IGLOO series and IGLOO devices refer to all of the IGLOO devices as listed in [Table 1-1](#). Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

### **ProASIC3 Terminology**

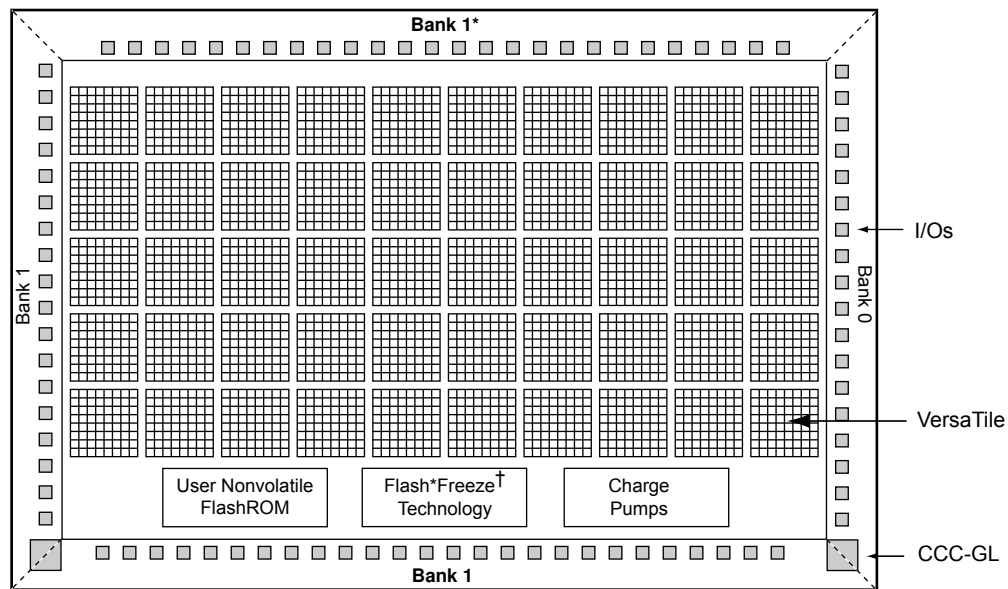
In documentation, the terms ProASIC3 series and ProASIC3 devices refer to all of the ProASIC3 devices as listed in [Table 1-1](#). Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

To further understand the differences between the IGLOO and ProASIC3 devices, refer to the [Industry's Lowest Power FPGAs Portfolio](#).

## Device Overview

Low power flash devices consist of multiple distinct programmable architectural features (Figure 1-5 on page 13 through Figure 1-7 on page 14):

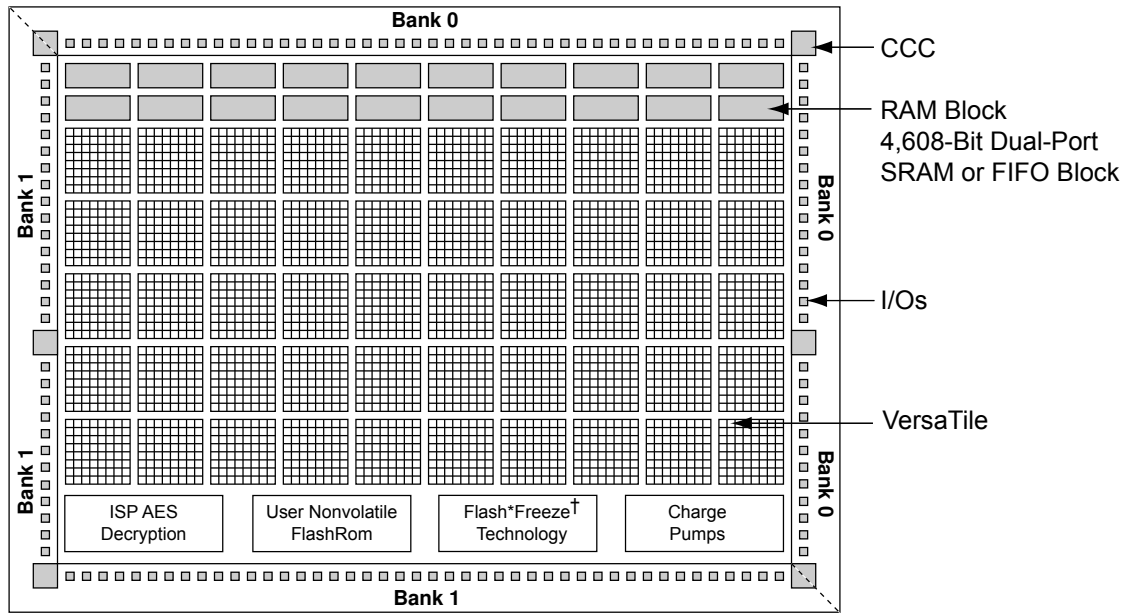
- FPGA fabric/core (VersaTiles)
- Routing and clock resources (VersaNets)
- FlashROM
- Dedicated SRAM and/or FIFO
  - 30 k gate and smaller device densities do not support SRAM or FIFO.
  - Automotive devices do not support FIFO operation.
- I/O structures
- Flash\*Freeze technology and low power modes



Notes: \* Bank 0 for the 30 k devices

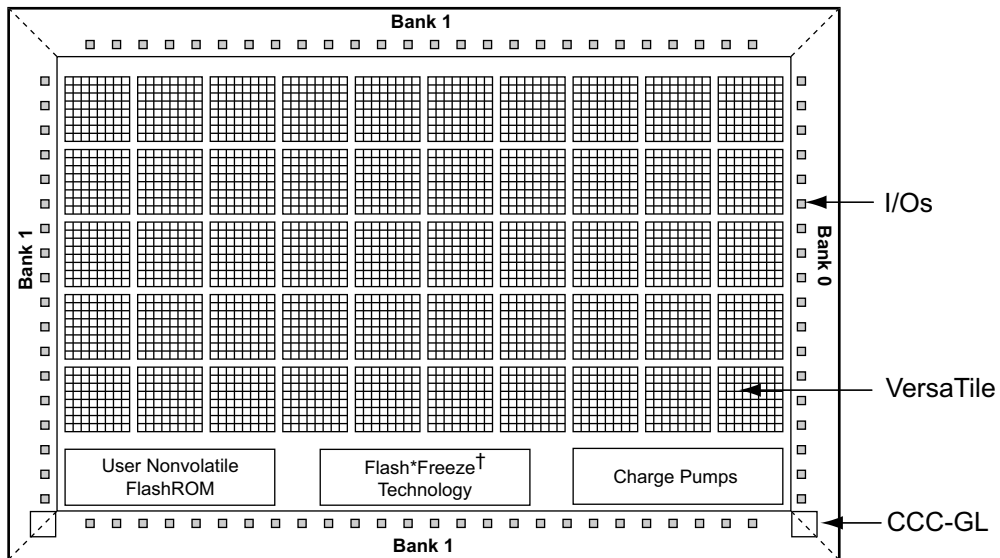
† Flash\*Freeze mode is supported on IGLOO devices.

**Figure 1-2 • IGLOO and ProASIC3 nano Device Architecture Overview with Two I/O Banks (applies to 10 k and 30 k device densities, excluding IGLOO PLUS devices)**



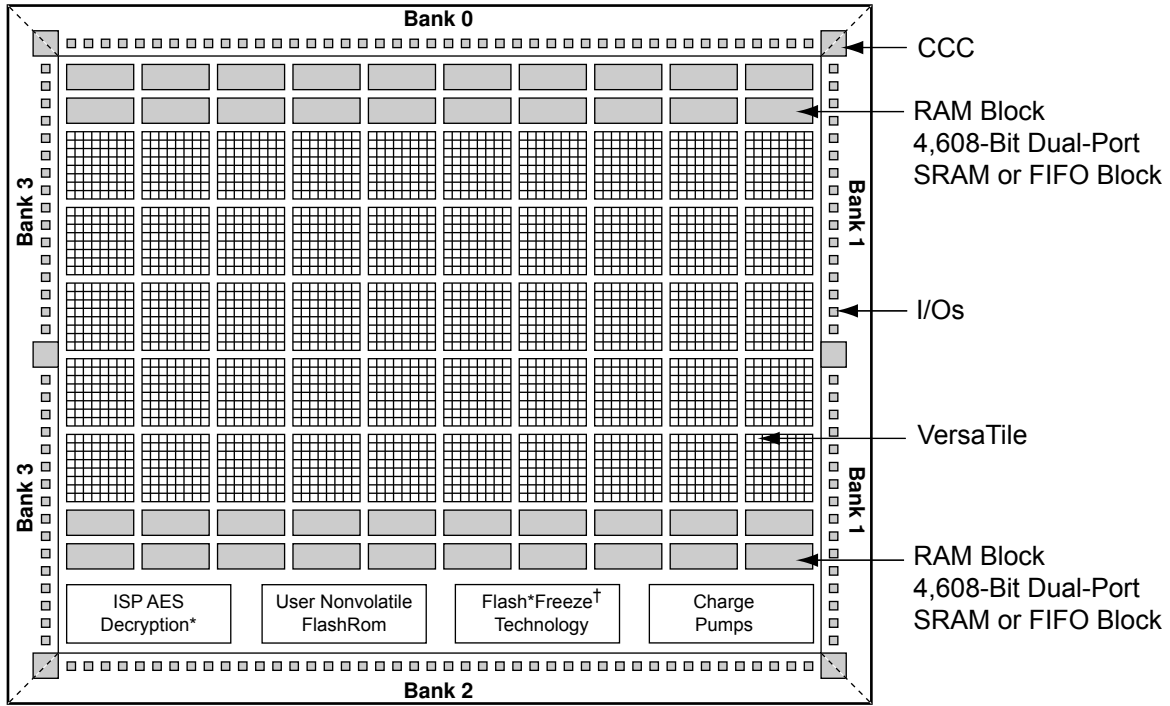
Note: † Flash\*Freeze mode is supported on IGLoo devices.

**Figure 1-3 • IGLoo Device Architecture Overview with Two I/O Banks with RAM and PLL (60 k and 125 k gate densities)**



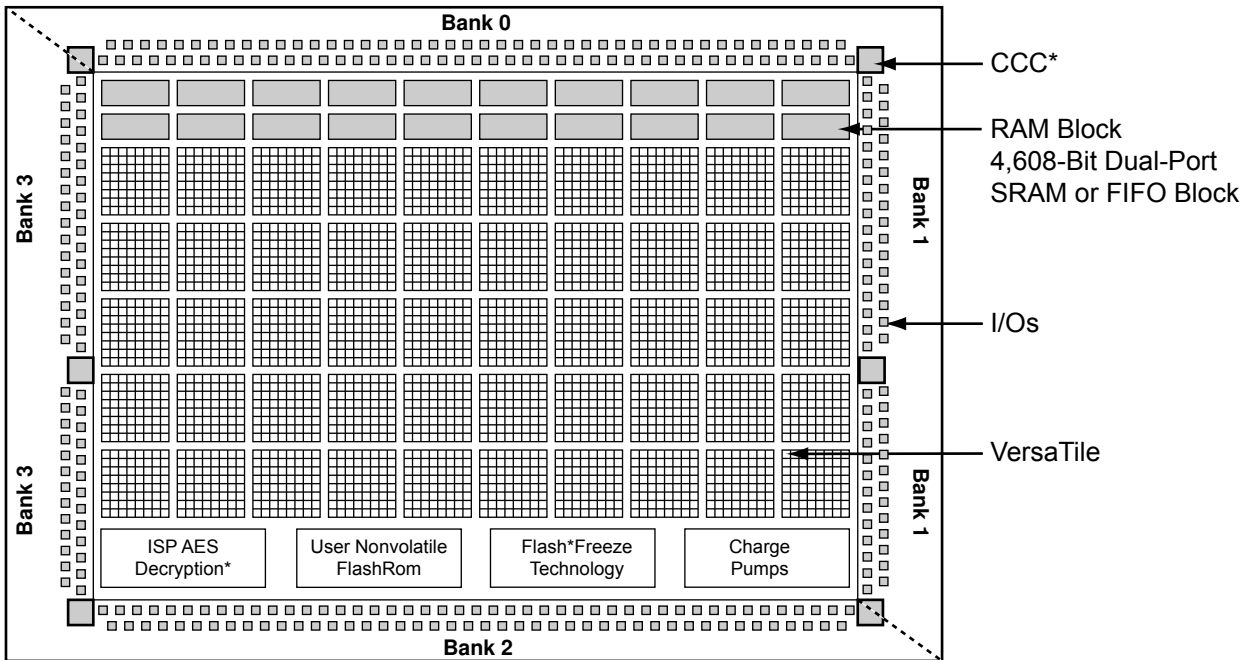
Note: † Flash\*Freeze mode is supported on IGLoo devices.

**Figure 1-4 • IGLoo Device Architecture Overview with Three I/O Banks (AGLN015, AGLN020, A3PN015, and A3PN020)**



Note: Flash\*Freeze technology only applies to IGLOO and ProASIC3L families.

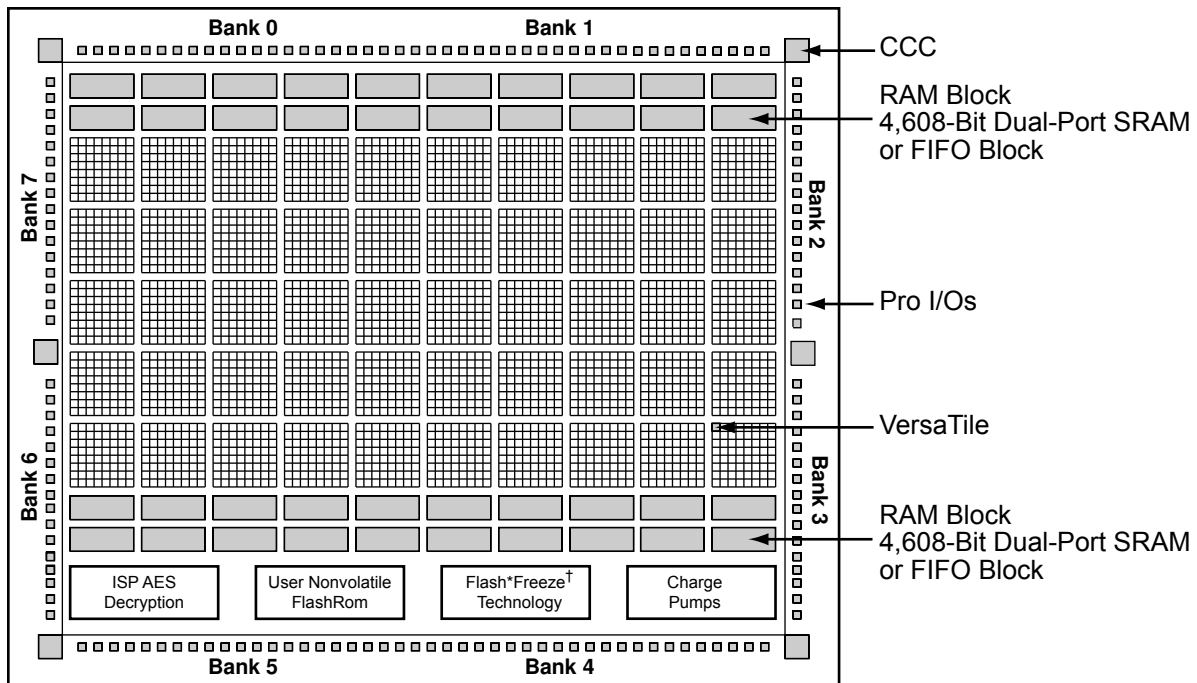
Figure 1-5 • IGLOO, IGLOO nano, ProASIC3 nano, and ProASIC3/L Device Architecture Overview with Four I/O Banks (AGL600 device is shown)



Note: \* AGLP030 does not contain a PLL or support AES security.

Figure 1-6 • IGLOO PLUS Device Architecture Overview with Four I/O Banks





*Note: Flash\*Freeze technology only applies to IGLOOe devices.*

**Figure 1-7 • IGLOOe and ProASIC3E Device Architecture Overview (AGLE600 device is shown)**

## I/O State of Newly Shipped Devices

Devices are shipped from the factory with a test design in the device. The power-on switch for VCC is OFF by default in this test design, so I/Os are tristated by default. Tristated means the I/O is not actively driven and floats. The exact value cannot be guaranteed when it is floating. Even in simulation software, a tristate value is marked as unknown. Due to process variations and shifts, tristated I/Os may float toward High or Low, depending on the particular device and leakage level.

If there is concern regarding the exact state of unused I/Os, weak pull-up/pull-down should be added to the floating I/Os so their state is controlled and stabilized.

## Core Architecture

### VersaTile

The proprietary IGLOO and ProASIC3 device architectures provide granularity comparable to gate arrays. The device core consists of a sea-of-VersaTiles architecture.

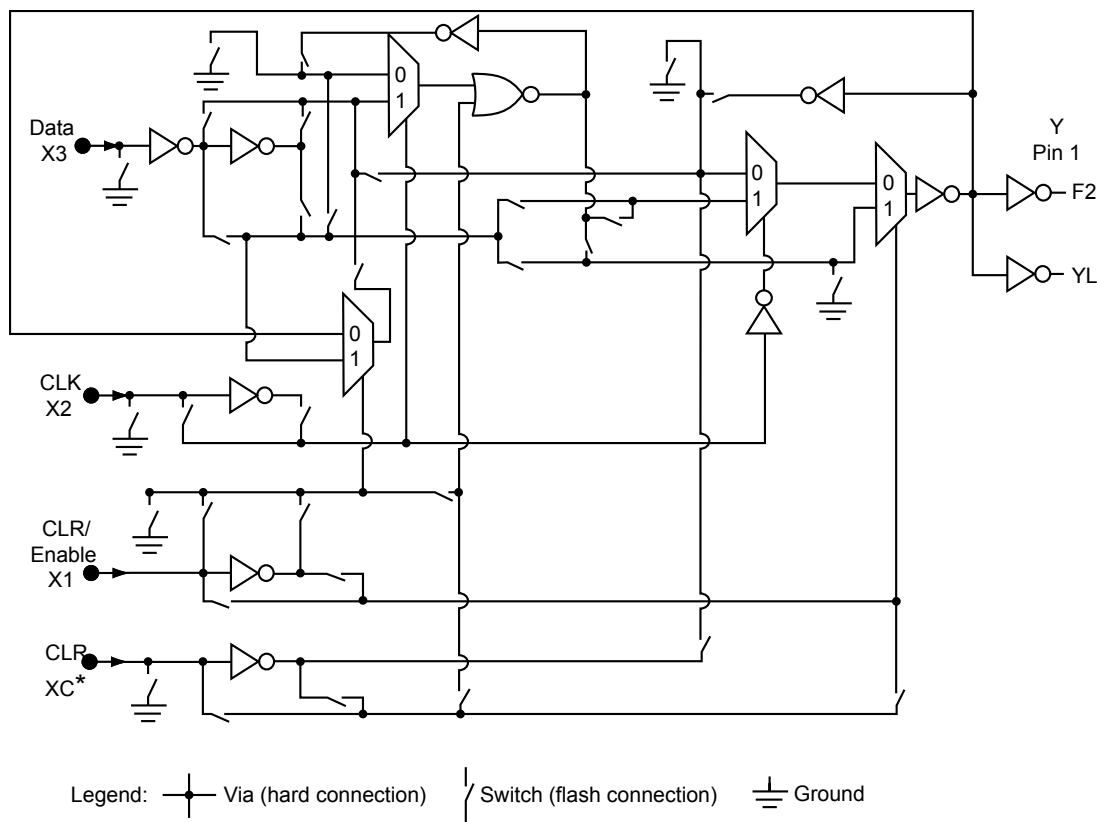
As illustrated in Figure 1-8, there are four inputs in a logic VersaTile cell, and each VersaTile can be configured using the appropriate flash switch connections:

- Any 3-input logic function
- Latch with clear or set
- D-flip-flop with clear or set
- Enable D-flip-flop with clear or set (on a 4<sup>th</sup> input)

VersaTiles can flexibly map the logic and sequential gates of a design. The inputs of the VersaTile can be inverted (allowing bubble pushing), and the output of the tile can connect to high-speed, very-long-line routing resources. VersaTiles and larger functions can be connected with any of the four levels of routing hierarchy.

When the VersaTile is used as an enable D-flip-flop, SET/CLR is supported by a fourth input. The SET/CLR signal can only be routed to this fourth input over the VersaNet (global) network. However, if, in the user's design, the SET/CLR signal is not routed over the VersaNet network, a compile warning will be given, and the intended logic function will be implemented by two VersaTiles instead of one.

The output of the VersaTile is F2 when the connection is to the ultra-fast local lines, or YL when the connection is to the efficient long-line or very-long-line resources.



\* This input can only be connected to the global clock distribution network.

Figure 1-8 • Low Power Flash Device Core VersaTile

## Array Coordinates

During many place-and-route operations in the Microsemi Designer software tool, it is possible to set constraints that require array coordinates. Table 1-2 provides array coordinates of core cells and memory blocks for IGLOO and ProASIC3 devices. Table 1-3 provides the information for IGLOO PLUS devices. Table 1-4 on page 17 provides the information for IGLOO nano and ProASIC3 nano devices. The array coordinates are measured from the lower left (0, 0). They can be used in region constraints for specific logic groups/blocks, designated by a wildcard, and can contain core cells, memories, and I/Os.

I/O and cell coordinates are used for placement constraints. Two coordinate systems are needed because there is not a one-to-one correspondence between I/O cells and core cells. In addition, the I/O coordinate system changes depending on the die/package combination. It is not listed in Table 1-2. The Designer ChipPlanner tool provides the array coordinates of all I/O locations. I/O and cell coordinates are used for placement constraints. However, I/O placement is easier by package pin assignment.

Figure 1-9 on page 17 illustrates the array coordinates of a 600 k gate device. For more information on how to use array coordinates for region/placement constraints, see the *Designer User's Guide* or online help (available in the software) for software tools.

**Table 1-2 • IGLOO and ProASIC3 Array Coordinates**

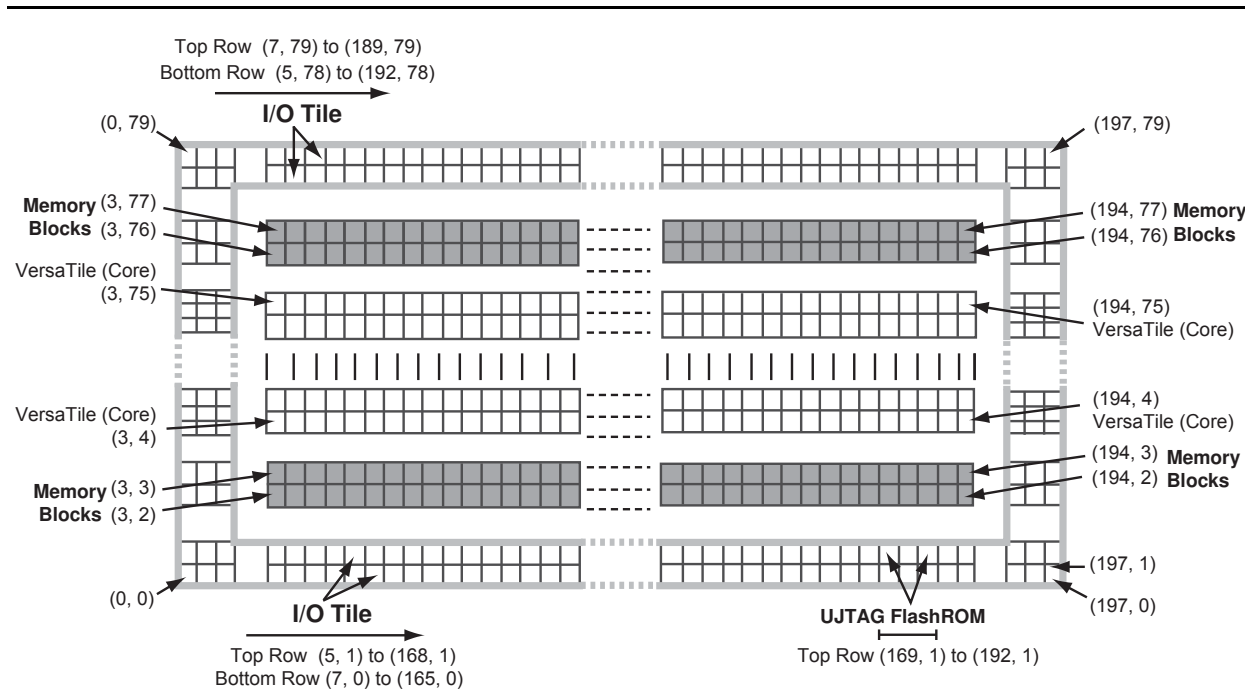
Device		VersaTiles				Memory Rows		Entire Die	
		Min.		Max.		Bottom	Top	Min.	Max.
IGLOO	ProASIC3/ ProASIC3L	x	y	x	y	(x, y)	(x, y)	(x, y)	(x, y)
AGL015	A3P015	3	2	34	13	None	None	(0, 0)	(37, 15)
AGL030	A3P030	3	3	66	13	None	None	(0, 0)	(69, 15)
AGL060	A3P060	3	2	66	25	None	(3, 26)	(0, 0)	(69, 29)
AGL125	A3P125	3	2	130	25	None	(3, 26)	(0, 0)	(133, 29)
AGL250	A3P250/L	3	2	130	49	None	(3, 50)	(0, 0)	(133, 53)
AGL400	A3P400	3	2	194	49	None	(3, 50)	(0, 0)	(197, 53)
AGL600	A3P600/L	3	4	194	75	(3, 2)	(3, 76)	(0, 0)	(197, 79)
AGL1000	A3P1000/L	3	4	258	99	(3, 2)	(3, 100)	(0, 0)	(261, 103)
AGLE600	A3PE600/L, RT3PE600L	3	4	194	75	(3, 2)	(3, 76)	(0, 0)	(197, 79)
	A3PE1500	3	4	322	123	(3, 2)	(3, 124)	(0, 0)	(325, 127)
AGLE3000	A3PE3000/L, RT3PE3000L	3	6	450	173	(3, 2) or (3, 4)	(3, 174) or (3, 176)	(0, 0)	(453, 179)

**Table 1-3 • IGLOO PLUS Array Coordinates**

Device		VersaTiles				Memory Rows		Entire Die	
		Min.		Max.		Bottom	Top	Min.	Max.
IGLOO PLUS		x	y	x	y	(x, y)	(x, y)	(x, y)	(x, y)
AGLP030		2	3	67	13	None	None	(0, 0)	(69, 15)
AGLP060		2	2	67	25	None	(3, 26)	(0, 0)	(69, 29)
AGLP125		2	2	131	25	None	(3, 26)	(0, 0)	(133, 29)

**Table 1-4 • IGLOO nano and ProASIC3 nano Array Coordinates**

Device		VersaTiles		Memory Rows		Entire Die	
		Min.	Max.	Bottom	Top	Min.	Max.
IGLOO nano	ProASIC3 nano	(x, y)	(x, y)	(x, y)	(x, y)	(x, y)	(x, y)
AGLN010	A3P010	(0, 2)	(32, 5)	None	None	(0, 0)	(34, 5)
AGLN015	A3PN015	(0, 2)	(32, 9)	None	None	(0, 0)	(34, 9)
AGLN020	A3PN020	(0, 2)	32, 13)	None	None	(0, 0)	(34, 13)
AGLN060	A3PN060	(3, 2)	(66, 25)	None	(3, 26)	(0, 0)	(69, 29)
AGLN125	A3PN125	(3, 2)	(130, 25)	None	(3, 26)	(0, 0)	(133, 29)
AGLN250	A3PN250	(3, 2)	(130, 49)	None	(3, 50)	(0, 0)	(133, 49)



*Note:* The vertical I/O tile coordinates are not shown. West-side coordinates are {(0, 2) to (2, 2)} to {(0, 77) to (2, 77)}; east-side coordinates are {(195, 2) to (197, 2)} to {(195, 77) to (197, 77)}.

**Figure 1-9 • Array Coordinates for AGL600, AGL600, A3P600, and A3PE600**

## Routing Architecture

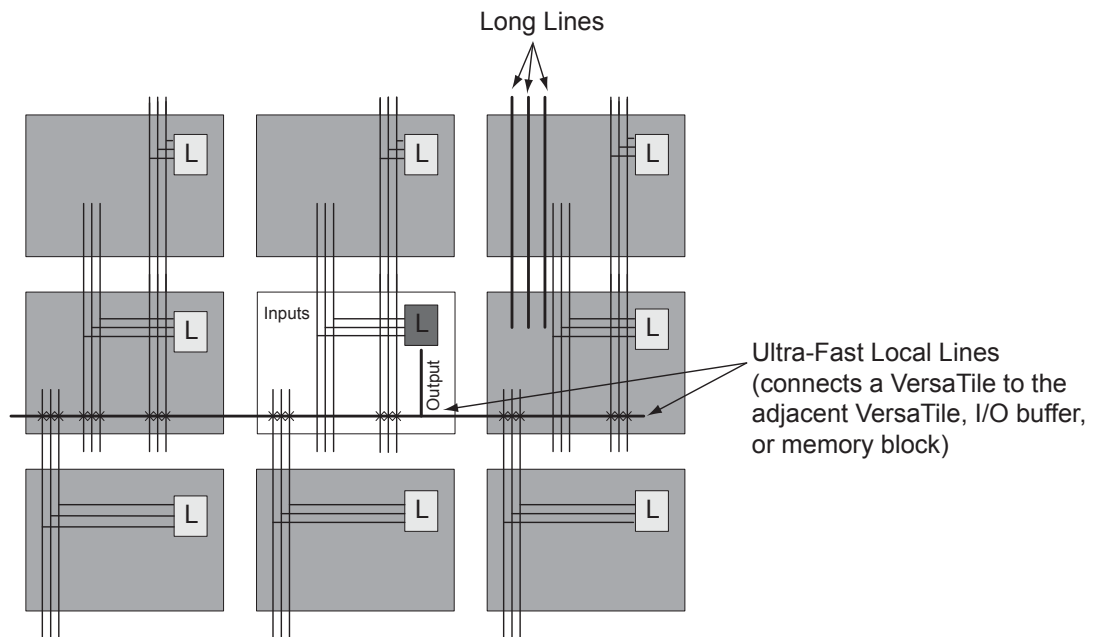
The routing structure of low power flash devices is designed to provide high performance through a flexible four-level hierarchy of routing resources: ultra-fast local resources; efficient long-line resources; high-speed, very-long-line resources; and the high-performance VersaNet networks.

The ultra-fast local resources are dedicated lines that allow the output of each VersaTile to connect directly to every input of the eight surrounding VersaTiles (Figure 1-10). The exception to this is that the SET/CLR input of a VersaTile configured as a D-flip-flop is driven only by the VersaNet global network.

The efficient long-line resources provide routing for longer distances and higher-fanout connections. These resources vary in length (spanning one, two, or four VersaTiles), run both vertically and horizontally, and cover the entire device (Figure 1-11 on page 19). Each VersaTile can drive signals onto the efficient long-line resources, which can access every input of every VersaTile. Routing software automatically inserts active buffers to limit loading effects.

The high-speed, very-long-line resources, which span the entire device with minimal delay, are used to route very long or high-fanout nets: length  $\pm 12$  VersaTiles in the vertical direction and length  $\pm 16$  in the horizontal direction from a given core VersaTile (Figure 1-12 on page 19). Very long lines in low power flash devices have been enhanced over those in previous ProASIC families. This provides a significant performance boost for long-reach signals.

The high-performance VersaNet global networks are low-skew, high-fanout nets that are accessible from external pins or internal logic. These nets are typically used to distribute clocks, resets, and other high-fanout nets requiring minimum skew. The VersaNet networks are implemented as clock trees, and signals can be introduced at any junction. These can be employed hierarchically, with signals accessing every input of every VersaTile. For more details on VersaNets, refer to the "Global Resources in Low Power Flash Devices" section on page 31.



*Note:* Input to the core cell for the D-flip-flop set and reset is only available via the VersaNet global network connection.

**Figure 1-10 • Ultra-Fast Local Lines Connected to the Eight Nearest Neighbors**

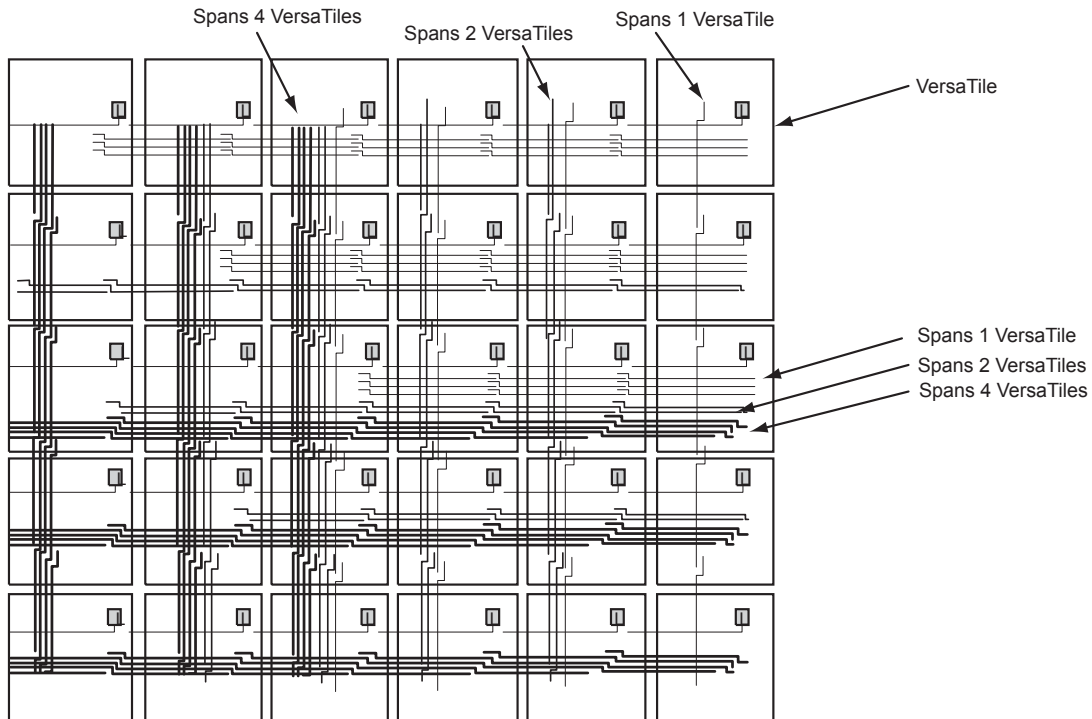


Figure 1-11 • Efficient Long-Line Resources

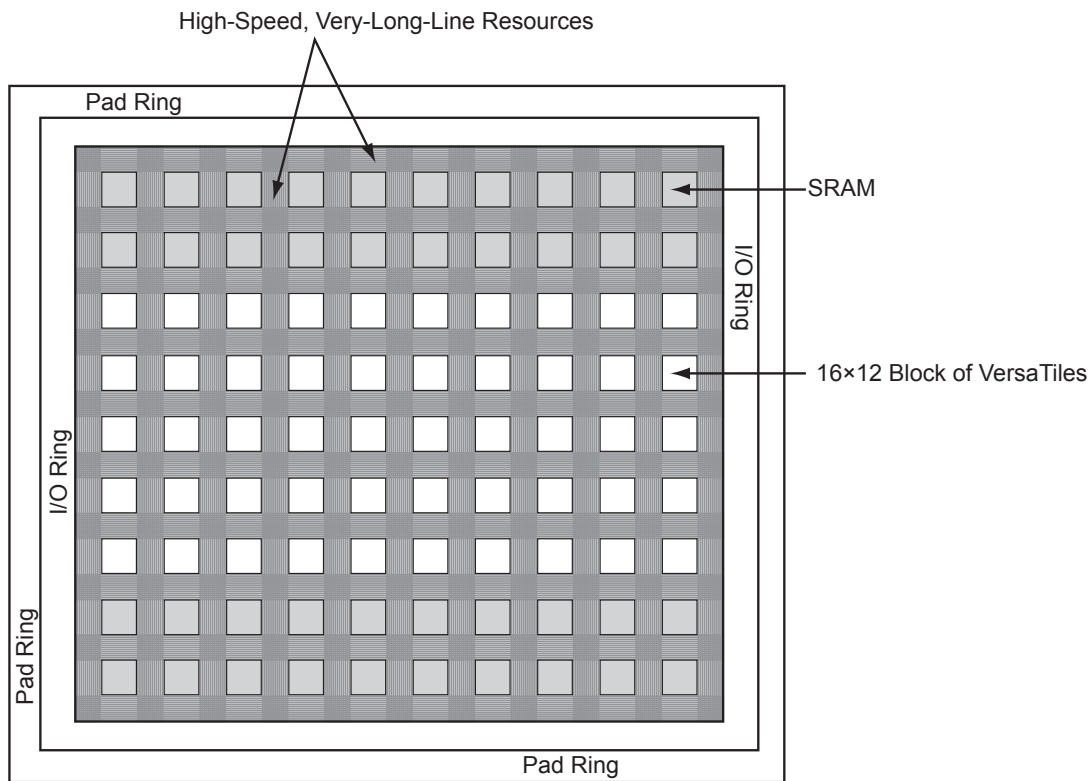


Figure 1-12 • Very-Long-Line Resources



## Related Documents

### User's Guides

*Designer User's Guide*

[http://www.microsemi.com/soc/documents/designer\\_ug.pdf](http://www.microsemi.com/soc/documents/designer_ug.pdf)

## List of Changes

The following table lists critical changes that were made in each revision of the chapter.

Date	Changes	Page
August 2012	The "I/O State of Newly Shipped Devices" section is new (SAR 39542).	14
July 2010	This chapter is no longer published separately with its own part number and version but is now part of several FPGA fabric user's guides.	N/A
v1.4 (December 2008)	IGLOO nano and ProASIC3 nano devices were added to <a href="#">Table 1-1 • Flash-Based FPGAs</a> .	10
	<a href="#">Figure 1-2 • IGLOO and ProASIC3 nano Device Architecture Overview with Two I/O Banks</a> (applies to 10 k and 30 k device densities, excluding IGLOO PLUS devices) through <a href="#">Figure 1-5 • IGLOO, IGLOO nano, ProASIC3 nano, and ProASIC3/L Device Architecture Overview with Four I/O Banks</a> (AGL600 device is shown) are new.	11, 12
	<a href="#">Table 1-4 • IGLOO nano and ProASIC3 nano Array Coordinates</a> is new.	17
v1.3 (October 2008)	The title of this document was changed from "Core Architecture of IGLOO and ProASIC3 Devices" to "FPGA Array Architecture in Low Power Flash Devices."	9
	The "FPGA Array Architecture Support" section was revised to include new families and make the information more concise.	10
	<a href="#">Table 1-2 • IGLOO and ProASIC3 Array Coordinates</a> was updated to include Military ProASIC3/EL and RT ProASIC3 devices.	16
v1.2 (June 2008)	The following changes were made to the family descriptions in <a href="#">Table 1-1 • Flash-Based FPGAs</a> : <ul style="list-style-type: none"> <li>• ProASIC3L was updated to include 1.5 V.</li> <li>• The number of PLLs for ProASIC3E was changed from five to six.</li> </ul>	10
v1.1 (March 2008)	<a href="#">Table 1-1 • Flash-Based FPGAs</a> and the accompanying text was updated to include the IGLOO PLUS family. The "IGLOO Terminology" section and "Device Overview" section are new.	10
	The "Device Overview" section was updated to note that 15 k devices do not support SRAM or FIFO.	11
	<a href="#">Figure 1-6 • IGLOO PLUS Device Architecture Overview with Four I/O Banks</a> is new.	13
	<a href="#">Table 1-2 • IGLOO and ProASIC3 Array Coordinates</a> was updated to add A3P015 and AGL015.	16
	<a href="#">Table 1-3 • IGLOO PLUS Array Coordinates</a> is new.	16

---

## 2 – Low Power Modes in ProASIC3/E and ProASIC3 nano FPGAs

---

### Introduction

The demand for low power systems and semiconductors, combined with the strong growth observed for value-based FPGAs, is driving growing demand for low power FPGAs. For portable and battery-operated applications, power consumption has always been the greatest challenge. The battery life of a system and on-board devices has a direct impact on the success of the product. As a result, FPGAs used in these applications should meet low power consumption requirements.

ProASIC<sup>®</sup>3/E and ProASIC3 nano FPGAs offer low power consumption capability inherited from their nonvolatile and live-at-power-up (LAPU) flash technology. This application note describes the power consumption and how to use different power saving modes to further reduce power consumption for power-conscious electronics design.

### Power Consumption Overview

In evaluating the power consumption of FPGA technologies, it is important to consider it from a system point of view. Generally, the overall power consumption should be based on static, dynamic, inrush, and configuration power. Few FPGAs implement ways to reduce static power consumption utilizing sleep modes.

SRAM-based FPGAs use volatile memory for their configuration, so the device must be reconfigured after each power-up cycle. Moreover, during this initialization state, the logic could be in an indeterminate state, which might cause inrush current and power spikes. More complex power supplies are required to eliminate potential system power-up failures, resulting in higher costs. For portable electronics requiring frequent power-up and -down cycles, this directly affects battery life, requiring more frequent recharging or replacement.

$$\text{SRAM-Based FPGA Total Power Consumption} = P_{\text{static}} + P_{\text{dynamic}} + P_{\text{inrush}} + P_{\text{config}} \quad \text{EQ 1}$$

$$\text{ProASIC3/E Total Power Consumption} = P_{\text{static}} + P_{\text{dynamic}} \quad \text{EQ 2}$$

Unlike SRAM-based FPGAs, Microsemi flash-based FPGAs are nonvolatile and do not require power-up configuration. Additionally, Microsemi nonvolatile flash FPGAs are live at power-up and do not require additional support components. Total power consumption is reduced as the inrush current and configuration power components are eliminated.

Note that the static power component can be reduced in flash FPGAs (such as the ProASIC3/E devices) by entering User Low Static mode or Sleep mode. This leads to an extremely low static power component contribution to the total system power consumption.

The following sections describe the usage of Static (Idle) mode to reduce the power component, User Low Static mode to reduce the static power component, and Sleep mode and Shutdown mode to achieve a range of power consumption when the FPGA or system is idle. [Table 2-1 on page 22](#) summarizes the different low power modes offered by ProASIC3/E devices.

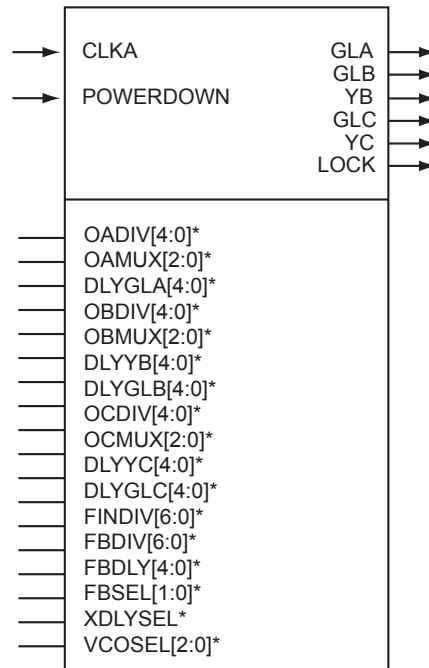
**Table 2-1 • ProASIC3/E/nano Low Power Modes Summary**

Mode	Power Supplies / Clock Status	Needed to Start Up
Active	On – All, clock Off – None	N/A (already active)
Static (Idle)	On – All Off – No active clock in FPGA  Optional: Enter User Low Static (Idle) Mode by enabling ULSICC macro to further reduce power consumption by powering down FlashROM.	Initiate clock source.  No need to initialize volatile contents.
Sleep	On – VCCI Off – VCC (core voltage), VJTAG (JTAG DC voltage), and VPUMP (programming voltage)  LAPU enables immediate operation when power returns.  Optional: Save state of volatile contents in external memory.	Need to turn on core.  Load states from external memory.  As needed, restore volatile contents from external memory.
Shutdown	On – None Off – All power supplies  Applicable to all ProASIC3 nano devices, cold-sparing and hot-insertion allow the device to be powered down without bringing down the system. LAPU enables immediate operation when power returns.	Need to turn on VCC, VCCI.

## Static (Idle) Mode

In Static (Idle) mode, the clock inputs are not switching and the static power consumption is the minimum power required to keep the device powered up. In this mode, I/Os are only drawing the minimum leakage current specified in the datasheet. Also, in Static (Idle) mode, embedded SRAM, I/Os, and registers retain their values, so the device can enter and exit this mode without any penalty.

If the embedded PLLs are used as the clock source, Static (Idle) mode can be entered easily by pulling LOW the PLL POWERDOWN pin (active-low). By pulling the PLL POWERDOWN pin to LOW, the PLL is turned off. Refer to [Figure 2-1 on page 23](#) for more information.



**Figure 2-1 • CCC/PLL Macro**

## User Low Static (Idle) Mode

User Low Static (Idle) mode is an advanced feature supported by ProASIC3/E devices to reduce static (idle) power consumption. Entering and exiting this mode is made possible using the ULSICC macro by setting its value to disable/enable the User Low Static (Idle) mode. Under typical operating conditions, characterization results show up to 25% reduction of the static (idle) power consumption. The greatest power savings in terms of percentage are seen in the smaller members of the ProASIC3 family. The active-high control signal for User Low Static (Idle) mode can be generated by internal or external logic. When the device is operating in User Low Static (Idle) mode, FlashROM functionality is temporarily disabled to save power. If FlashROM functionality is needed, the device can exit User Low Static mode temporarily and re-enter the mode once the functionality is no longer needed.

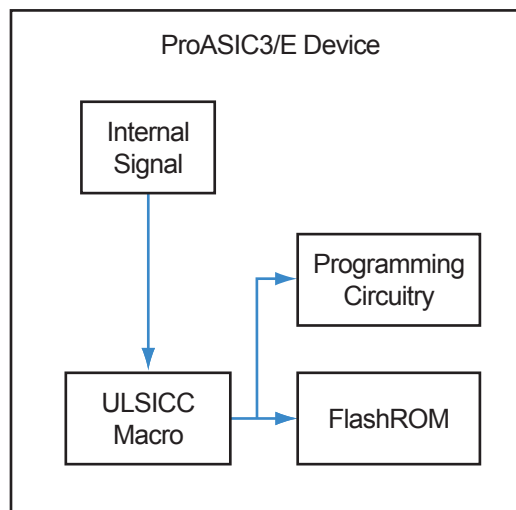
To utilize User Low Static (Idle) mode, simply instantiate the ULSICC macro ([Table 2-2 on page 24](#)) in your design, and connect the input port to either an internal logic signal or a device package pin, as illustrated in [Figure 2-2 on page 24](#) or [Figure 2-3 on page 25](#), respectively. The attribute is used so the Synplify<sup>®</sup> synthesis tool will not optimize the instance with no output port.

This mode can be used to lower standard static (idle) power consumption when the FlashROM feature is not needed. Configuring the device to enter User Low Static (Idle) mode is beneficial when the FPGA enters and exits static mode frequently and lowering power consumption as much as possible is desired. The device is still functional, and data is retained in this state so the device can enter and exit this mode quickly, resulting in reduced total power consumption. The device can also stay in User Low Static mode when the FlashROM feature is not used in the device.

**Table 2-2 • Using ULSICC Macro\***

VHDL	Verilog
<pre> COMPONENT ULSICC   port (     LSICC      : in    STD_ULOGIC); END COMPONENT;  Example: COMPONENT ULSICC   port (     LSICC      : in    STD_ULOGIC); END COMPONENT;  attribute syn_noprune : boolean; attribute syn_noprune of u1 : label is true; u1: ULSICC port map(myInputSignal);                     </pre>	<pre> module ULSICC(LSICC);   input LSICC; endmodule  Example: ULSICC U1(.LSICC(myInputSignal)) /* synthesis syn_noprune=1 */;                     </pre>

*Note:* \*Supported in Libero® software v7.2 and newer versions.


**Figure 2-2 • User Low Static (Idle) Mode Application—Internal Control Signal**

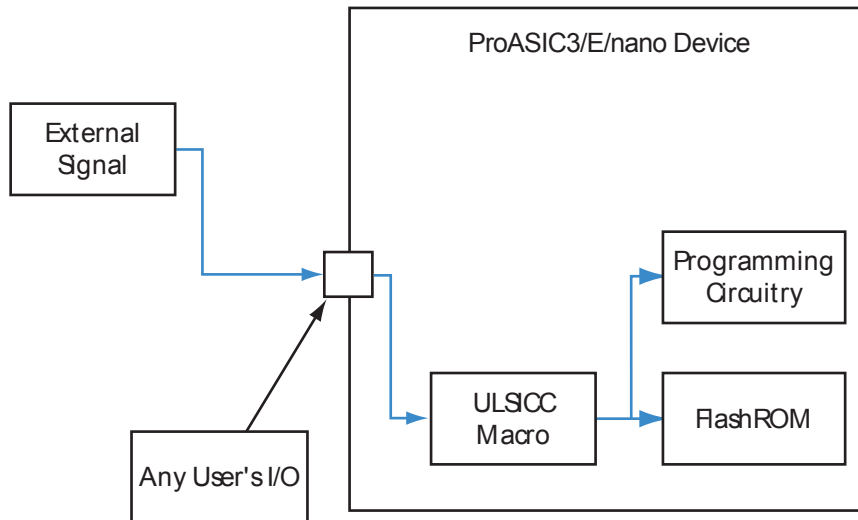


Figure 2-3 • User Low Static (Idle) Mode Application—External Control Signal

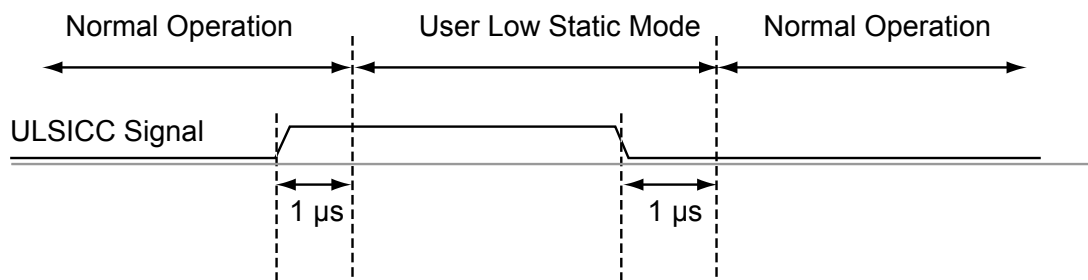


Figure 2-4 • User Low Static (Idle) Mode Timing Diagram

## Sleep Mode

ProASIC3/E and ProASIC3 nano FPGAs support Sleep mode when device functionality is not required. In Sleep mode, the VCC (core voltage), VJTAG (JTAG DC voltage), and VPUMP (programming voltage) are grounded, resulting in the FPGA core being turned off to reduce power consumption. While the ProASIC3/E device is in Sleep mode, the rest of the system is still operating and driving the input buffers of the ProASIC3/E device. The driven inputs do not pull up power planes, and the current draw is limited to a minimal leakage current.

Table 2-3 shows the status of the power supplies in Sleep mode. When a power supply is powered off, the corresponding power pin can be left floating or grounded.

Table 2-3 • Sleep Mode—Power Supply Requirements for ProASIC3/E/nano Devices

Power Supplies	ProASIC3/E/nano Device
VCC	Powered off
VCCI = VMV	Powered on
VJTAG	Powered off
VPUMP	Powered off